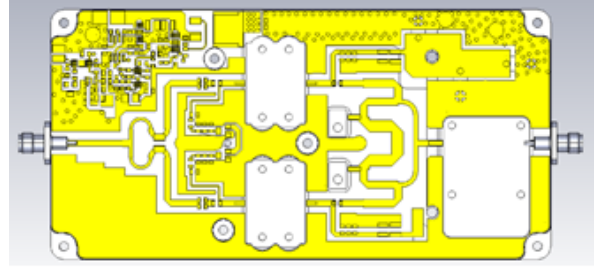


# RAP2729P60; 2.7 GHz – 2.9 GHz 1 kW

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Small Dimensions & Light Weight
- Fast Switching Capability



## ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

<b>Frequency:</b>	2.7-2.9 GHz
<b>Output Power:</b>	1000 W Typ. %10 300 $\mu$ s
<b>Nominal Gain:</b>	10.5 dB
<b>Gain Flatness:</b>	$\pm 1$ dB
<b>Input VSWR:</b>	2:1 max.
<b>Load VSWR for Survival:</b>	$\infty$ :1
<b>DC Supply Voltage:</b>	50 V
<b>Efficiency:</b>	% 55 Min.
<b>Enable Speed:</b>	1 $\mu$ s max.
<b>Pulse Droop :</b>	0.5 dB
<b>Rise / Fall Time</b>	50 nsec max.
<b>Operating Case Temp.:</b>	-40 °C to 85 °C
<b>Storage Temperature:</b>	-40 °C to 85 °C
<b>Shock:</b>	MIL-STD-810F, 516.5
<b>Vibration:</b>	MIL-STD-810F, 514.5

## INTERFACES

<b>RF Input:</b>	SMA Female
<b>RF Output:</b>	SMA Female
<b>50 V :</b>	Solder Pad
<b>GND :</b>	Solder Pad
<b>Enable :</b>	Solder Pad

## MECHANICAL SPECIFICATIONS

<b>Size (mm) :</b>	145.7 x 70
<b>(inch) :</b>	5.74 x 2.76
<b>Weight :</b>	275 gr.
<b>Plating :</b>	Yellow Chromate

